产品概览

NTBG015N065SC1: Silicon Carbide MOSFET, N-Channel, 650V, 15.3 mΩ ， D2PAK-7L

欲看完整文档，请参阅数据表。

Silicon Carbide (SiC) MOSFET uses a completely new technology that provide superior switching performance and higher reliability compared to Silicon. In addition, the low ON resistance and compact chip size ensure low capacitance and gate charge. Consequently, system benefits include highest efficiency, faster operation frequency, increased power density, reduced EMI, and reduced system size.

特性

- Low RDSon
- High Junction Temperature
- 100% UIL Tested
- RoHS Compliant
- High Speed Switching and Low Capacitance
- 650V rated
- Max RDS(on) = 18.4 mΩ at Vgs = 18V, Id = 60A

优势

- 15.3 mΩ
- Tj = 175°C

应用

- DC-DC Converter
- Boost Inverter

终端产品

- UPS
- Solar
- Power Supply

器件电气规格

产品	Pricing ($/Unit)	Compliance	Status	Channel Polarity	Configuration	Blocking Voltage BV_{DSS} (V)	$I_{D(max)}$ (A)	$R_{DS(on)}$ Typ @ 25°C (mΩ)	Q_g Total (C)	Output Capacitance (C)	T_j Max (°C)	Package Type
NTBG015N065SC1	15.6881	Pb-free Halide free non AEC-Q and PPAP	Active	N-Channel	Single	650	176	15.3	250	397	175	D2PAK7 (TO-263-7L HV)

欲了解更多信息，请联系您当地的销售支援 www.onsemi.cn 。

创建于：9/21/2021